## NSN 5961-01-194-3094

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Inclosure Material:
Metal
Overall Length:
2.637 inches
Mounting Facility Quantity:
1
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-83
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case and quality assurance level txv
Overall Width Across Flats:
1.227 inches
Thread Size:
0.500 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
300.0 repetitive peak reverse voltage and 300.0 repetitive peak off-state voltage and 400.0 nonrepetitive peak reverse voltage
Current Rating Per Characteristic:
50.00 amperes forward current, total rms universal
Power Rating Per Characteristic:
5.0 watts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
125.0 degrees celsius ambient air
Special Features:
Junction pattern arrangement: pnpn
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designator:
Unf
Terminal Type And Quantity:
2 tab, solder lug and 1 threaded stud
Specification Data:
81349-mil-s-19500/204 government specification
Shalf Life:

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N/a

**Unit Of Measure:** 

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Demilitarization:

No

Fiig:

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